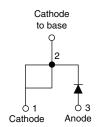


# HEXFRED® Ultrafast Soft Recovery Diode, 8 A





PRODUCT SUMMARY					
Package	TO-220AC				
I <sub>F(AV)</sub>	8 A				
$V_{R}$	1200 V				
V <sub>F</sub> at I <sub>F</sub>	2.4 V				
t <sub>rr</sub> typ.	28 ns				
T <sub>J</sub> max.	150 °C				
Diode variation	Single die				

#### **FEATURES**

- · Ultrafast and ultrasoft recovery
- Very low I<sub>RRM</sub> and Q<sub>rr</sub>
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





ROHS COMPLIANT HALOGEN FREE

#### **BENEFITS**

- · Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- · Reduced snubbing
- Reduced parts count

#### **DESCRIPTION**

VS-HFA08TB120HN3 is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 8 A continuous current, the VS-HFA08TB120HN3 is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (IRRM) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA08TB120HN3 is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and mumany other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Cathode to anode voltage	V <sub>R</sub>		1200	V			
Maximum continuous forward current	I <sub>F</sub>	T <sub>C</sub> = 100 °C	8				
Single pulse forward current	I <sub>FSM</sub>		130	Α			
Maximum repetitive forward current	I <sub>FRM</sub>		32				
Maximum naviar dissination	В	T <sub>C</sub> = 25 °C	73.5	10/			
Maximum power dissipation	P <sub>D</sub>	T <sub>C</sub> = 100 °C	29	W			
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +150	°C			



<b>ELECTRIACL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Cathode to anode breakdown voltage	V <sub>BR</sub>	Ι <sub>R</sub> = 100 μΑ	1200	-	-			
Maximum forward voltage	V <sub>FM</sub>	I <sub>F</sub> = 8.0 A	-	2.6	3.3	V		
		I <sub>F</sub> = 16 A	-	3.4	4.3			
		I <sub>F</sub> = 8.0 A, T <sub>J</sub> = 125 °C	-	2.4	3.1			
Maximum reverse		$V_R = V_R$ rated	-	0.31	10			
leakage current	I <sub>RM</sub>	$T_J = 125 ^{\circ}\text{C}, V_R = 0.8 \text{x} \text{V}_R \text{rated}$	-	135	1000	- μΑ		
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 200 V	=	11	20	pF		
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8.0	-	nH		

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS	
	t <sub>rr</sub>	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A}$	A/μs, V <sub>R</sub> = 30 V	-	28	-	ns - A	
Reverse recovery time	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	63	-		
	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C	I <sub>F</sub> = 8.0 A dI <sub>F</sub> /dt = 200 A/µs	-	106	-		
Peak recovery current	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C		-	4.5	-		
reak recovery current	I <sub>RRM2</sub>	T <sub>J</sub> = 125 °C		-	6.2	-		
Reverse recovery charge	Q <sub>rr1</sub>	T <sub>J</sub> = 25 °C	$V_R = 200 \text{ V}$	-	140	-	nC	
neverse recovery charge	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	335	-	IIC	
Peak rate of recovery current during t <sub>b</sub>	dI <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C		-	133	-	- A/μs	
	dI <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		-	85	-	Ανμδ	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	-	300	°C	
Thermal resistance, junction to case	R <sub>thJC</sub>		-	-	1.7		
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Typical socket mount	-	-	40	K/W	
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.25	-		
Weight			-	6.0	-	g	
vveignt			-	0.21	-	oz.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style TO-220AC	HFA08TB120H				

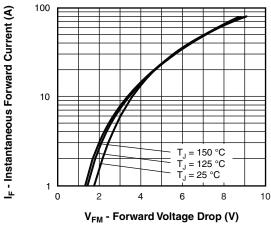


Fig. 1 - Maximum Forward Voltage Drop Characteristics

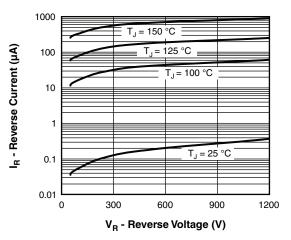


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

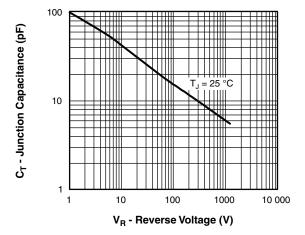


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

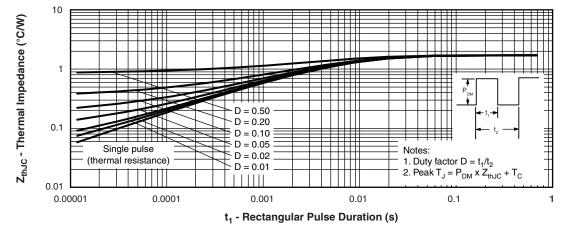


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

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## Vishay Semiconductors

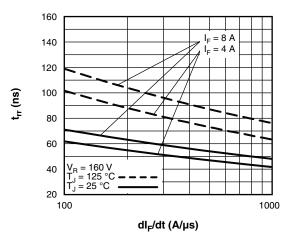


Fig. 5 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

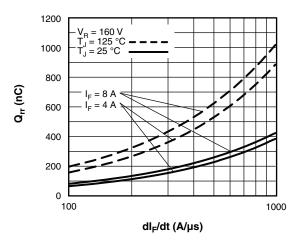


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

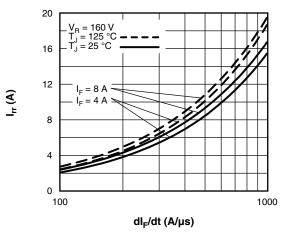


Fig. 6 - Typical Recovery Current vs. dI<sub>F</sub>/dt

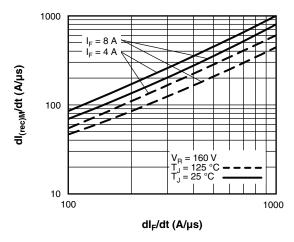
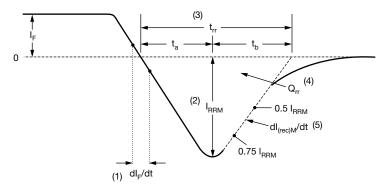


Fig. 8 - Typical dl<sub>(rec)M</sub>/dt vs. dl<sub>F</sub>/dt



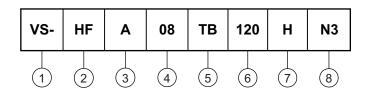
- (1) dl<sub>F</sub>/dt rate of change of current through zero crossing
- (2) I<sub>RRM</sub> peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm I_F$  to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{\rm rr}$  area under curve defined by  $\mathbf{t}_{\rm rr}$  and  $\mathbf{I}_{\rm RRM}$ 
  - $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$
- (5) dl<sub>(rec)M</sub>/dt peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 9 - Reverse Recovery Waveform and Definitions



#### **ORDERING INFORMATION TABLE**

Device code



1 - Vishay Semiconductors product

2 - HEXFRED® family

Electron irradiated

4 - Current rating (08 = 8 A)

5 - Package:

TB = TO-220AC

6 - Voltage rating (120 = 1200 V)

- H = AEC-Q101 qualified

8 - Environmental digit:

N3 = halogen-free, RoHS-compliant, and totally lead (Pb)-free

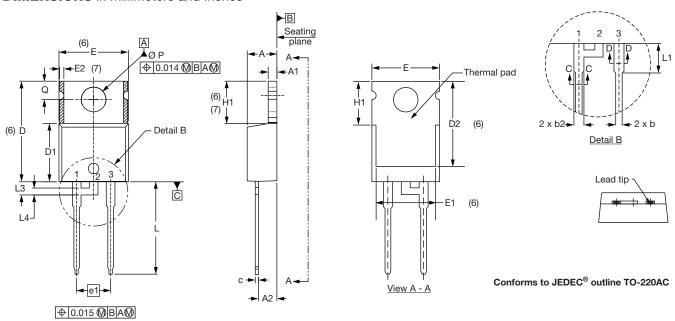
ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-HFA08TB120HN3	50	1000	Antistatic plastic tube			

LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95221</u>					
Part marking information	www.vishay.com/doc?95068				



## **TO-220AC**

#### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIM	IETERS	INCHES		NOTES
STINIBUL	MIN.	MAX.	MIN.	MAX.	NOIES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6
E	10.11	10.51	0.398	0.414	3, 6

SYMBOL	MILLIN	IETERS	INCHES		NOTES
STINIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
E1	6.86	8.89	0.270	0.350	6
E2	-	0.76	-	0.030	7
e1	4.88	5.28	0.192	0.208	
H1	5.84	6.86	0.230	0.270	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
L3	1.78	2.13	0.070	0.084	
L4	0.76	1.27	0.030	0.050	2
ØΡ	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	

#### Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimension: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- $^{(7)}$  Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, D2 (minimum) where dimensions are derived from the actual package outline



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